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***DISCRETE POWER DIODES and THYRISTORS***  
***DATA BOOK***

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## ST300C..C SERIES

### PHASE CONTROL THYRISTORS

### Hockey Puk Version

#### Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (E-PUK)

#### Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

#### Major Ratings and Characteristics

Parameters	ST300C..C	Units
$I_{T(AV)}$	650	A
@ $T_{hs}$	55	°C
$I_{T(RMS)}$	1290	A
@ $T_{hs}$	25	°C
$I_{TSM}$	@ 50Hz	8000
	@ 60Hz	8380
$I^2t$	@ 50Hz	320
	@ 60Hz	292
$V_{DRM}/V_{RRM}$	400 to 2000	V
$t_q$ typical	100	μs
$T_J$	- 40 to 125	°C

650A



case style TO-200AB (E-PUK)

## ST300C..C Series

### ELECTRICAL SPECIFICATIONS

#### Voltage Ratings

Type number	Voltage Code	$V_{DRM}/V_{RRM}$ , max. repetitive peak and off-state voltage V	$V_{RSM}$ , maximum non-repetitive peak voltage V	$I_{DRM}/I_{RRM}$ max. @ $T_J = T_J$ max mA
ST300C..C	04	400	500	50
	08	800	900	
	12	1200	1300	
	16	1600	1700	
	18	1800	1900	
	20	2000	2100	

#### On-state Conduction

Parameter	ST300C..C	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	650 (320)	A	180° conduction, half sine wave double side (single side) cooled
	55 (75)	°C	
$I_{T(RMS)}$ Max. RMS on-state current	1290	A	DC @ 25°C heatsink temperature double side cooled
$I_{TSM}$ Max. peak, one-cycle non-repetitive surge current	8000		t = 10ms No voltage
	8380		t = 8.3ms reapplied
	6730		t = 10ms 100% $V_{RRM}$
	7040		t = 8.3ms reapplied
$I^2t$ Maximum $I^2t$ for fusing	320		t = 10ms No voltage
	292		t = 8.3ms reapplied
	226		t = 10ms 100% $V_{RRM}$
	207		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	3200	$KA^2\sqrt{s}$	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	0.97	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J$ max.
$V_{T(TO)2}$ High level value of threshold voltage	0.98		$(I > \pi \times I_{T(AV)}), T_J = T_J$ max.
$r_{t1}$ Low level value of on-state slope resistance	0.74	$m\Omega$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J$ max.
$r_{t2}$ High level value of on-state slope resistance	0.73		$(I > \pi \times I_{T(AV)}), T_J = T_J$ max.
$V_{TM}$ Max. on-state voltage	2.18	V	$I_{pk} = 1635A, T_J = T_J$ max, $t_p = 10ms$ sine pulse
$I_H$ Maximum holding current	600	mA	$T_J = 25^\circ C$ , anode supply 12V resistive load
$I_L$ Typical latching current	1000		

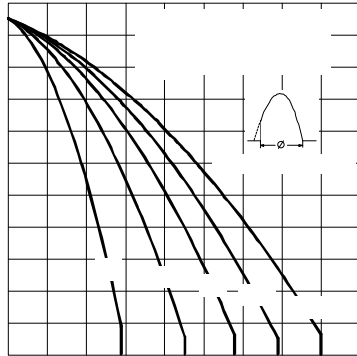


Fig. 3 - Current Ratings Characteristics

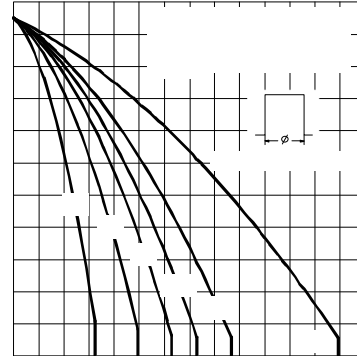


Fig. 4 - Current Ratings Characteristics

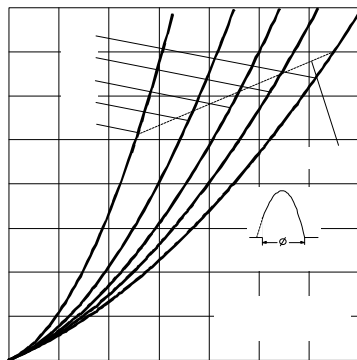


Fig. 5 - On-state Power Loss Characteristics

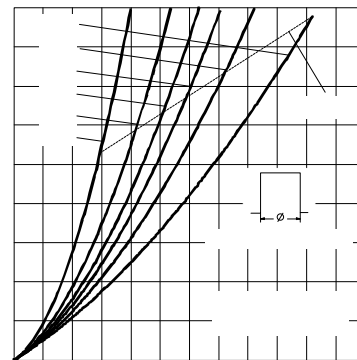


Fig. 6 - On-state Power Loss Characteristics

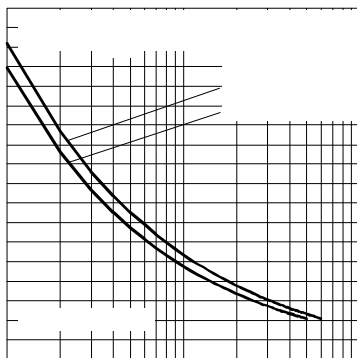


Fig. 7 - Maximum Non-Repetitive Surge Current  
Single and Double Side Cooled

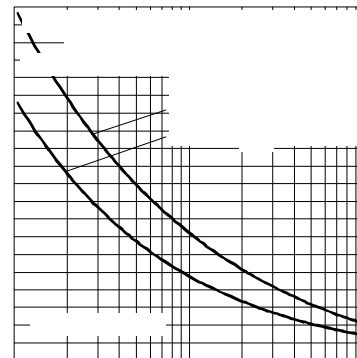


Fig. 8 - Maximum Non-Repetitive Surge Current  
Single and Double Side Cooled

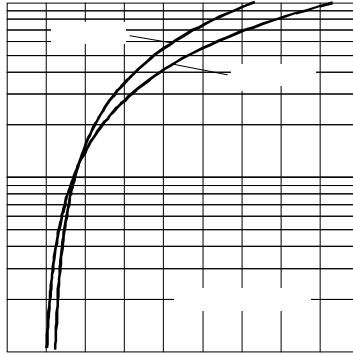


Fig. 9 - On-state Voltage Drop Characteristics

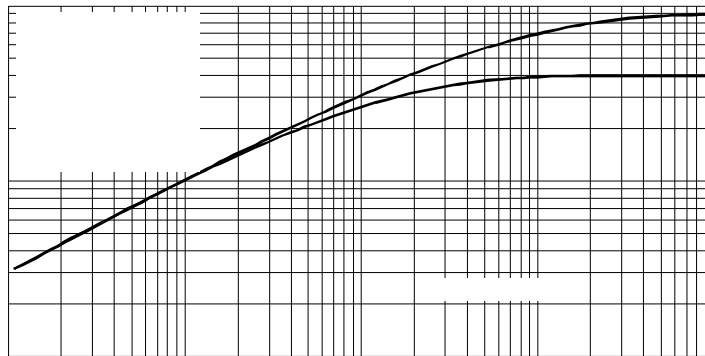


Fig. 10 - Thermal Impedance  $Z_{thJ-hs}$  Characteristics

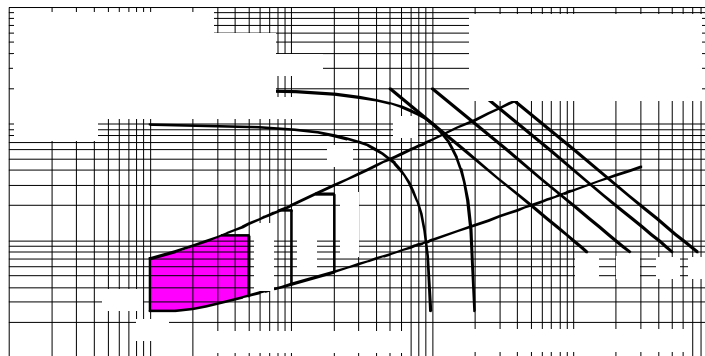


Fig. 11 - Gate Characteristics

## Switching

Parameter	ST300C..C	Units	Conditions
$di/dt$ Max. non-repetitive rate of rise of turned-on current	1000	A/ $\mu$ s	Gate drive 20V, 20 $\Omega$ , $t_r \leq 1\mu$ s $T_J = T_J \text{ max}$ , anode voltage $\leq 80\% V_{DRM}$
$t_d$ Typical delay time	1.0	$\mu$ s	Gate current 1A, $di_g/dt = 1\text{A}/\mu$ s $V_d = 0.67\% V_{DRM}$ , $T_J = 25^\circ\text{C}$
$t_q$ Typical turn-off time	100		$I_{TM} = 300\text{A}$ , $T_J = T_J \text{ max}$ , $di/dt = 40\text{A}/\mu$ s, $V_R = 50\text{V}$ $dv/dt = 20\text{V}/\mu$ s, Gate 0V 100 $\Omega$ , $t_p = 500\mu$ s

## Blocking

Parameter	ST300C..C	Units	Conditions
$dv/dt$ Maximum critical rate of rise of off-state voltage	500	V/ $\mu$ s	$T_J = T_J \text{ max}$ , linear to 80% rated $V_{DRM}$
$I_{RRM}$ $I_{DRM}$ Max. peak reverse and off-state leakage current	50	mA	$T_J = T_J \text{ max}$ , rated $V_{DRM}/V_{RRM}$ applied

## Triggering

Parameter		ST300C..C		Units	Conditions	
P <sub>GM</sub>	Maximum peak gate power	10.0		W	T <sub>J</sub> = T <sub>J</sub> max, t <sub>p</sub> ≤ 5ms	
P <sub>G(AV)</sub>	Maximum average gate power	2.0			T <sub>J</sub> = T <sub>J</sub> max, f = 50Hz, d% = 50	
I <sub>GM</sub>	Max. peak positive gate current	3.0		A	T <sub>J</sub> = T <sub>J</sub> max, t <sub>p</sub> ≤ 5ms	
+V <sub>GM</sub>	Maximum peak positive gate voltage	20		V	T <sub>J</sub> = T <sub>J</sub> max, t <sub>p</sub> ≤ 5ms	
-V <sub>GM</sub>	Maximum peak negative gate voltage	5.0				
I <sub>GT</sub>	DC gate current required to trigger	TYP.	MAX.	mA	Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied	
		200	-			
		100	200			
		50	-			
V <sub>GT</sub>	DC gate voltage required to trigger	2.5	-	V		T <sub>J</sub> = - 40°C
		1.8	3.0			T <sub>J</sub> = 25°C
		1.1	-		T <sub>J</sub> = 125°C	
I <sub>GD</sub>	DC gate current not to trigger	10.0		mA	Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V <sub>DRM</sub> anode-to-cathode applied	
V <sub>GD</sub>	DC gate voltage not to trigger	0.25				V

# ST300C..C Series

## Thermal and Mechanical Specification

Parameter	ST300C..C	Units	Conditions
T <sub>J</sub> Max. operating temperature range	-40 to 125	°C	
T <sub>stg</sub> Max. storage temperature range	-40 to 150		
R <sub>thJ-hs</sub> Max. thermal resistance, junction to heatsink	0.09 0.04	K/W	DC operation single side cooled DC operation double side cooled
R <sub>thC-hs</sub> Max. thermal resistance, case to heatsink	0.02 0.01	K/W	DC operation single side cooled DC operation double side cooled
F Mounting force, ± 10%	9800 (1000)	N (Kg)	
wt Approximate weight	83	g	
Case style	TO - 200AB (E-PUK)		See Outline Table

## ΔR<sub>thJ-hs</sub> Conduction

(The following table shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.010	0.011	0.007	0.007	K/W	T <sub>J</sub> = T <sub>J</sub> max.
120°	0.012	0.012	0.012	0.013		
90°	0.015	0.015	0.016	0.017		
60°	0.022	0.022	0.023	0.023		
30°	0.036	0.036	0.036	0.037		

## Ordering Information Table

Device Code							
ST	30	0	C	20	C	1	
1	2	3	4	5	6	7	8
1	- Thyristor						
2	- Essential part number						
3	- 0 = Converter grade						
4	- C = Ceramic Puk						
5	- Voltage code: Code x 100 = V <sub>RRM</sub> (See Voltage Rating Table)						
6	- C = Puk Case TO-200AB (E-PUK)						
7	- 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads) 1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads) 2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads) 3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)						
8	- Critical dv/dt: None = 500V/μsec (Standard value) L = 1000V/μsec (Special selection)						

Outline Table

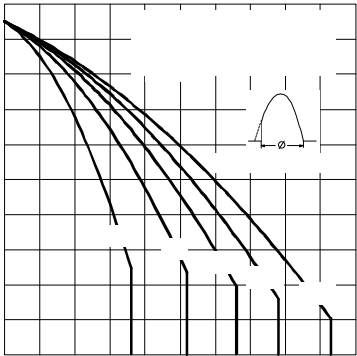
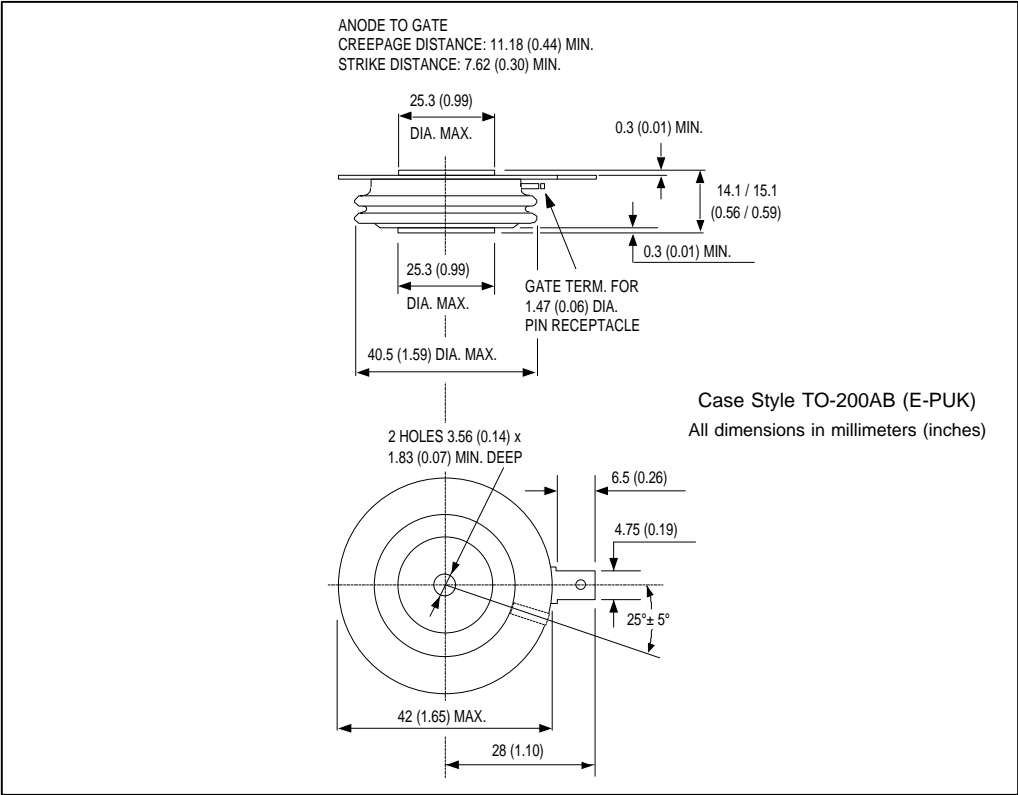


Fig. 1 - Current Ratings Characteristics

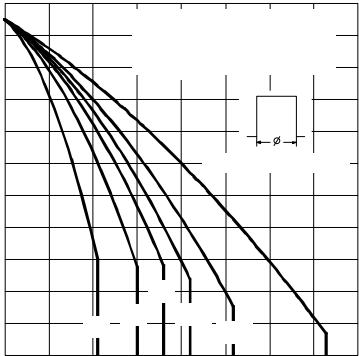


Fig. 2 - Current Ratings Characteristics